



JS80R850U

主要参数 MAIN CHARACTERISTICS

I_D	6.6A
V_{DS}	800 V
$R_{DS(on)-Typ}$ (@ $V_{GS}=10V$)	750m Ω
Q_g-typ	9.5 nC

用途

- 高频开关电源
- 电子镇流器
- LED 电源

产品特性

- 低栅极电荷
- 低 C_{RSS} (典型值 11pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

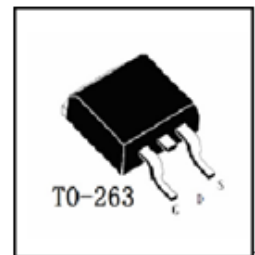
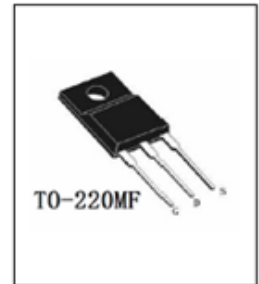
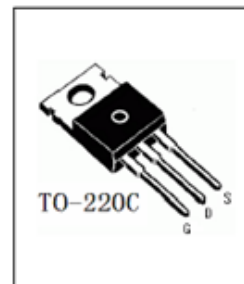
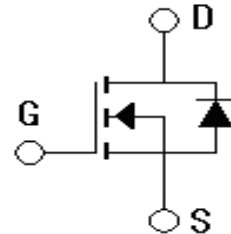
APPLICATIONS

- High frequency switching mode power supply
- Electronic ballast
- LED power supply

FEATURES

- Low gate charge
- Low C_{RSS} (typical 9pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订 货 型 号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JS80R850CU-C-B	JS80R850CU-C-BR	N/A	N/A	JS80R850C	TO-220C
JS80R850FU-F2-B	JS80R850FU-F2-BR	N/A	N/A	JS80R850F	TO-220MF-K2
JS80R850SU-S-B	JS80R850SU-S-BR	JS80R850U-S-A	JS80R850U-S-AR	JS80R850S	TO-263





绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value		单 位 Unit
		JS80R850CU/SU	JS80R850FU	
最高漏极—源极直流电压 Drain-Source Voltage	V_{DSS}	800		V
连续漏极电流 Drain Current -continuous	I_D T=25℃	6.6*		A
	T=100℃	4.2*		A
最大脉冲漏极电流 (注 1) Drain Current - pulse (note 1)	I_{DM}	20*		A
最高栅源电压 Gate-Source Voltage	V_{GSS}	±30		V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E_{AS}	80		mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I_{AR}	1.6		A
重复雪崩能量 (注 1) Repetitive Avalanche Energy (note 1)	E_{AR}	0.2		mJ
二极管反向恢复最大电压变 化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	15		V/ns
耗散功率 Power Dissipation	P_D T _C =25℃	63	31	W
	-Derate above 25℃	0.50	0.25	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T _J , T _{STG}	-55~+150		℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	300		℃

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature





电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单 位 Units
关态特性 Off –Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	800	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, referenced to $25^\circ C$	-	0.65	-	V/ $^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=800V, V_{GS}=0V, T_C=25^\circ C$	-	-	10	μA
		$V_{DS}=800V, T_C=125^\circ C$	-	-	100	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.5	3.5	4.5	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=7.5A$	-	750	850	m Ω
正向跨导 Forward Transconductance	g_{fs}	$V_{DS}=40V, I_D=7A$ (note 4)	-	6	-	S
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=100KHz$	-	380	-	pF
输出电容 Output capacitance	C_{oss}		-	115	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	9	-	pF





电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=400V, I_D=3.5A, R_G=25\Omega,$	-	23	-	ns	
上升时间 Turn-On rise time	t_r	$V_{GS}=10V$	-	18	-	ns	
延迟时间 Turn-Off delay time	$t_{d(off)}$	(note 4, 5)	-	44	-	ns	
下降时间 Turn-Off Fall time	t_f		-	18	-	ns	
栅极电荷总量 Total Gate Charge	Q_g	$V_{DS}=450V,$	-	9.5	-	nC	
栅-源电荷 Gate-Source charge	Q_{gs}	$I_D=3.5A$	-	2.0	-	nC	
栅-漏电荷 Gate-Drain charge	Q_{gd}	$V_{GS}=10V$ (note 4, 5)	-	4.5	-	nC	
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current		I_S	-	-	7	A	
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}	-	-	20	A	
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=3.5A$	-	0.9	1.5	V	
反向恢复时间 Reverse recovery time	t_{rr}	$V_{GS}=0V, I_S=3.5A$	-	190	-	ns	
反向恢复电荷 Reverse recovery charge	Q_{rr}	$dI_F/dt=100A/\mu s$ (note 4)	-	2.3	-	μC	

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max		单 位 Unit
		JS80R850CU/SU	JS80R850FU	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	5.0	3.9	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	62.5	80	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2: $V_{GS}=10V, V_{DD}=50V, R_G=25\Omega$, 起始结温 $T_J=25^{\circ}C$
- 3: $I_{SD}\leq 6.6A, di/dt\leq 300A/\mu s, V_{DD}\leq BV_{DSS}$, 起始结温 $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度 $\leq 300\mu s$, 占空比 $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

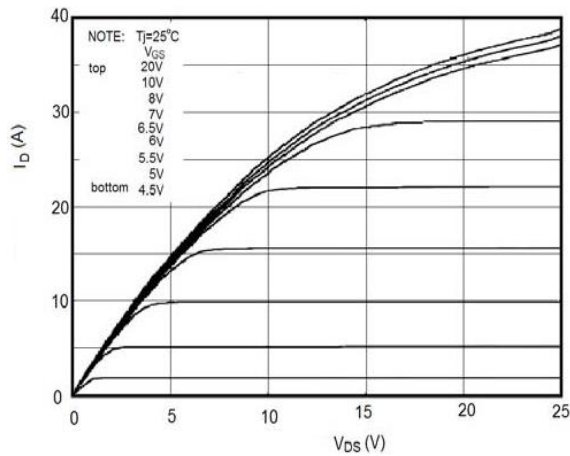
- 1: Pulse width limited by maximum junction temperature
- 2: $V_{GS}=10V, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^{\circ}C$
- 3: $I_{SD}\leq 6.6A, di/dt\leq 300A/\mu s, V_{DD}\leq BV_{DSS}$, Starting $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
- 5: Essentially independent of operating temperature



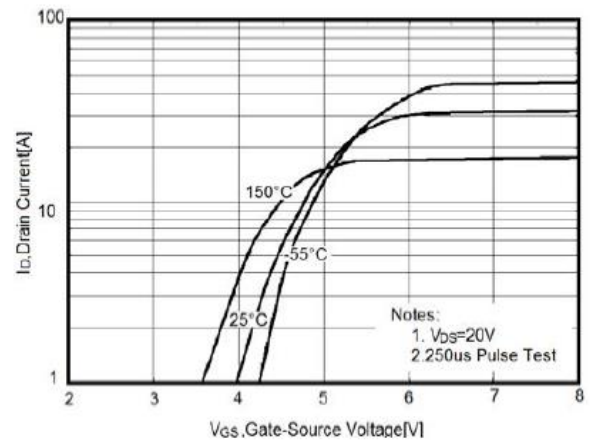


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

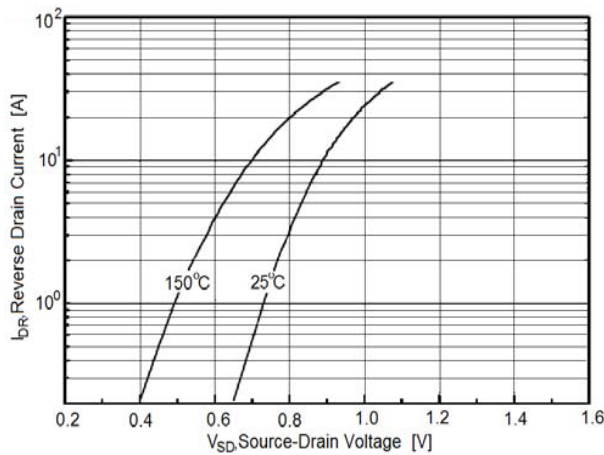
On-Region Characteristics



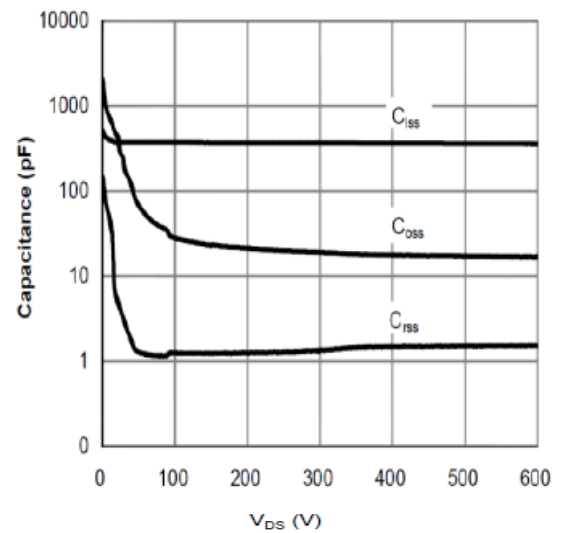
Transfer Characteristics



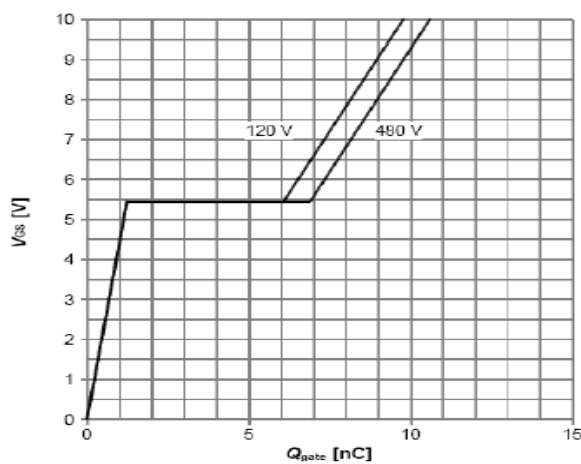
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics

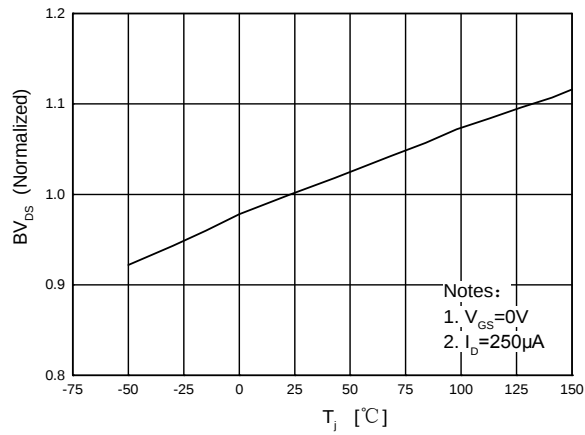
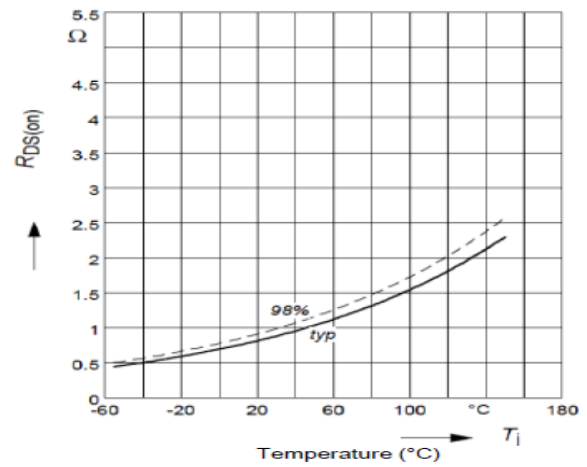
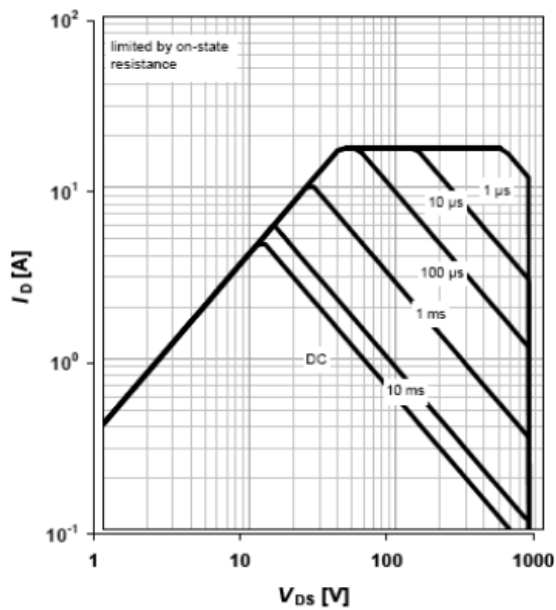
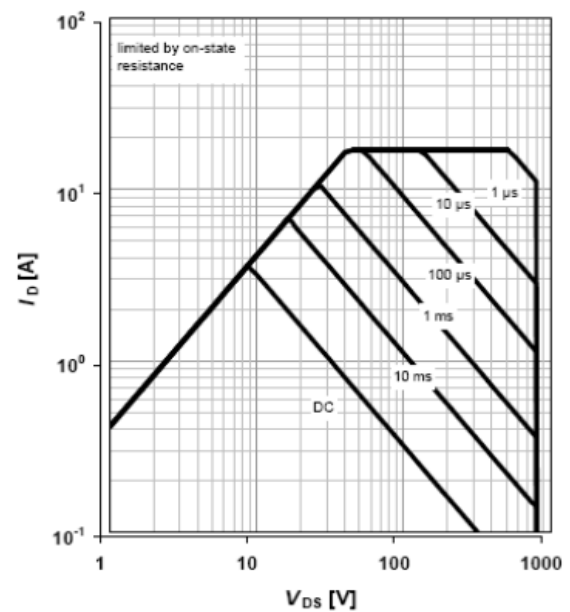


Gate Charge Characteristics

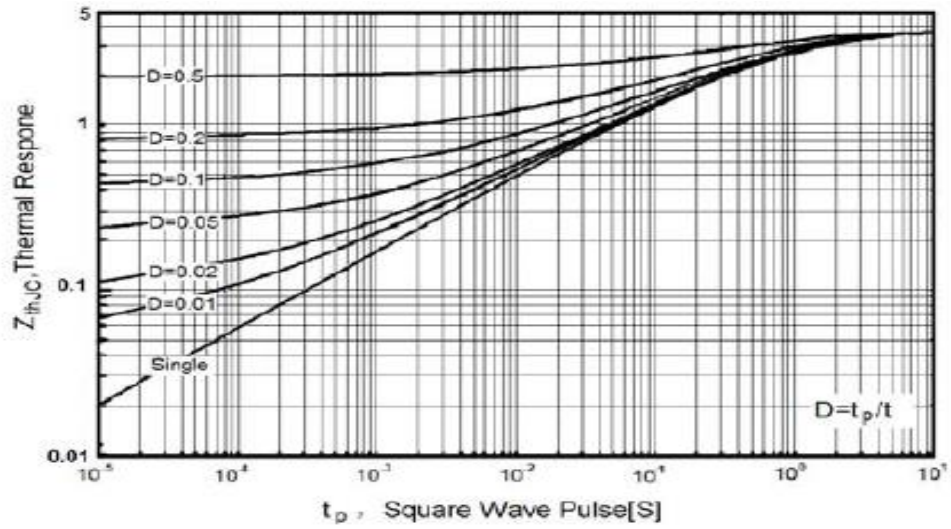




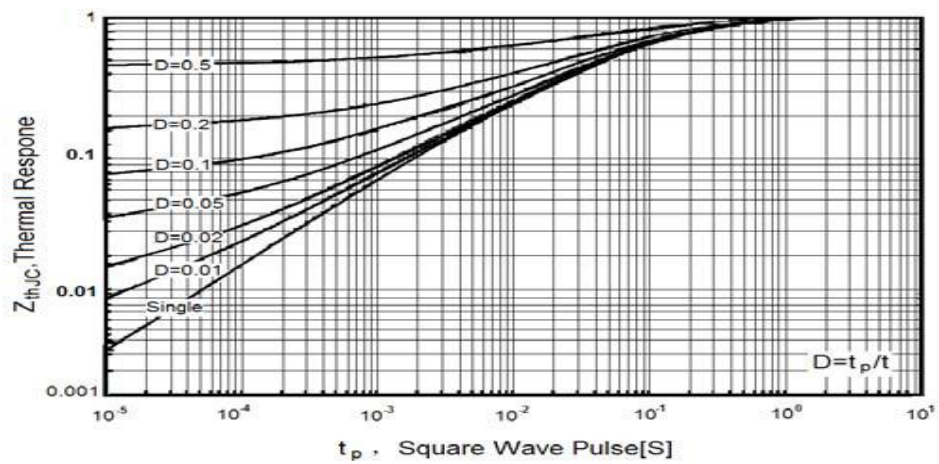
特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Breakdown Voltage Variation
vs. TemperatureOn-Resistance Variation
vs. TemperatureMaximum Safe Operating Area
For JS80R850CU/SUMaximum Safe Operating Area
For JS80R850FU

Transient Thermal Response Curve For JS80R850CU/SU



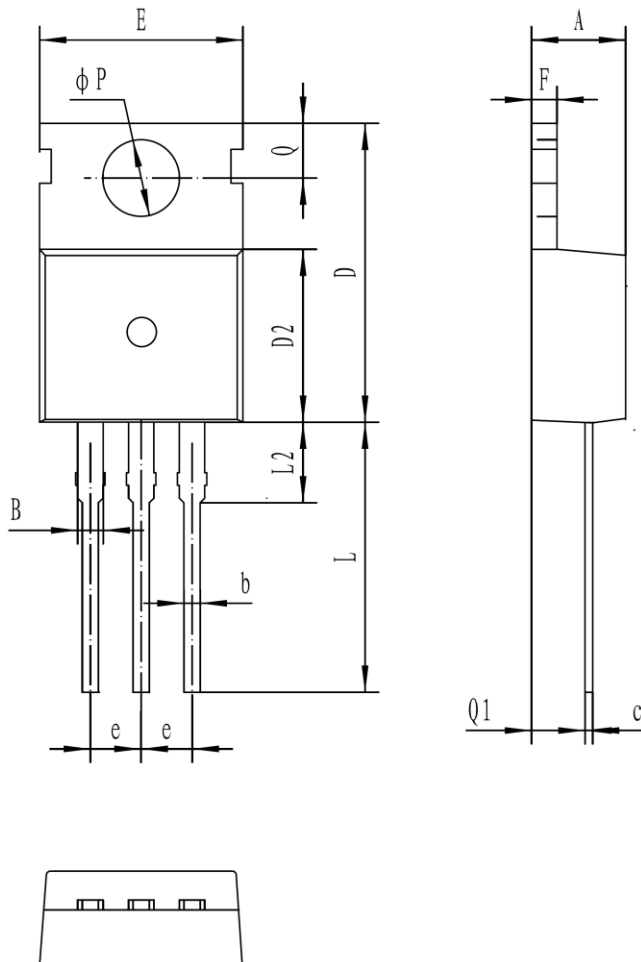
Transient Thermal Response Curve For JS80R850FU





TO-220C

单位 Unit: mm



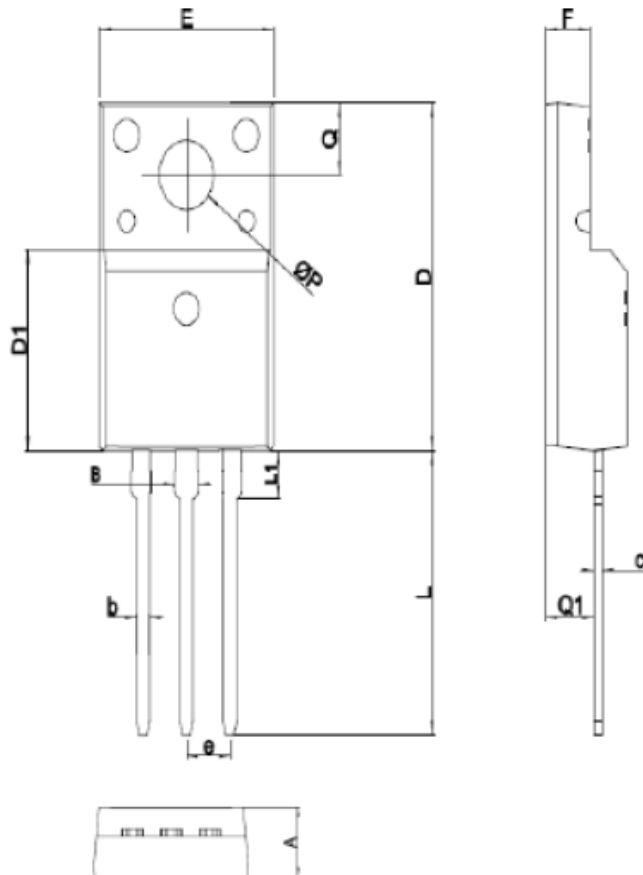
符号 symbol	MIN	MAX
A	4.30	4.70
B	1.10	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80





TO-220MF-K2

单位 Unit: mm



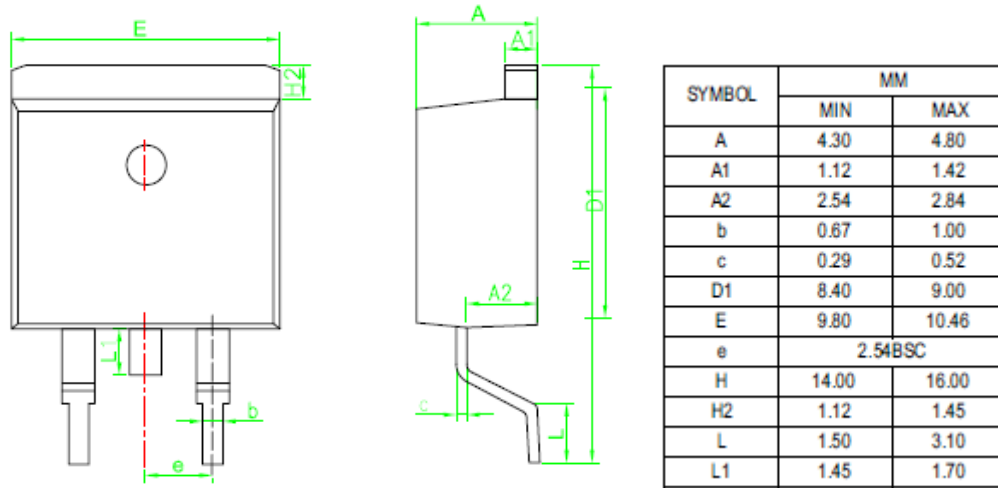
SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B		1.27
b	0.59	0.79
c	0.45	0.60
D	15.67	16.07
D1	8.97	9.37
e	2.54TYPE	
E	9.96	10.36
F	2.34	2.74
L	12.65	13.35
L1	1.80	2.20
Q	3.2	3.4
Q1	2.56	2.96
ΦP	3.08	3.28



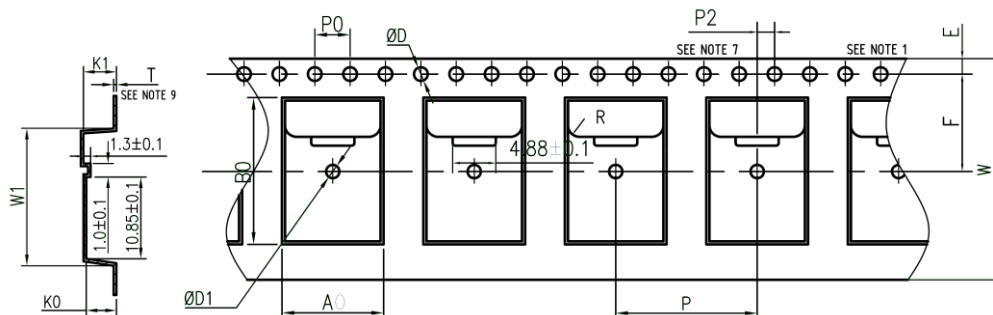


TO-263

单位 Unit: mm



编带 REEL



NOTES

1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE 0.2mm;
任意10个传输孔间距累积误差0.2mm;
2. MATERIAL: BLACK CONDUCTIVE POLYSTYRENE;
材料: 黑色防静电聚苯乙烯;
3. DIMENSIONS ARE IN mm (UNLESS OTHERWISE SPECIFIED);
除非特别标注, 尺寸单位为毫米;
4. K0 MEASURED FROM A PLANE ON THE INSIDE BOTTOM OF THE POCKET TO THE TOP SURFACE ON THE CARRIER;
K0是从凹槽底部上表面到载带顶面的测量尺寸;
5. A0 AND B0 MEASURED ON A PLANE 0.30mm ABOVE THE BOTTOM OF THE POCKET;
从凹槽底部上方测量A0和B0的平面度是0.30mm;
6. SURFACE RESISTIVITY IS BETWEEN 1×10^6 TO 1×10^{10} OHMS/SQUARE;
表面电阻 $1 \times 10^6 \sim 1 \times 10^{10} \Omega/\square$;
7. Allowable Camber to be 1 mm/100 mm
载带100mm以内, 弯曲度不可超过1mm。

外观		尺寸	
P0	4.0±0.1	W	
P2	2.0±0.1	A0	
P	16.0±0.1	E	
T	0.35±0.05	F	
K0	4.85±0.1	D	
B0	16.3±0.1	D1	
POCKET;		W1	规格1
			规格2





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3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知

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2. We strongly recommend customers check carefully on the trademark when buying our product, if there is any question, please don't be hesitate to contact us.
3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
4. Jilin Sino-microelectronics co., Ltd reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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